CLAIMS

1. A chemical mechanical polishing slurry, comprising abrasive particles, oxidants, amino acids, quaternary ammonium bases and water, and the pH of said chemical mechanical polishing slurry is alkaline, wherein the weight concentration of said quaternary ammonium bases is in the range of 5-12% and wherein said abrasive particles are one or more selected from a group consisting of SiO_2、Al_2O_3、ZrO_2、CeO_2、SiC、Fe_2O_3、TiO_2 and /or Si_3N_4.
2. A chemical mechanical polishing slurry of Claim 1, wherein the weight concentration of said abrasive particles is in the range of 1-30%.
3. A chemical mechanical polishing slurry of Claim 1, wherein said oxidants are one or more selected from a group consisting of bromate, chlorate, iodate, periodic acid and/or periodate.
4. A chemical mechanical polishing slurry of Claim 3, wherein said bromate is potassium bromate, said chlorate is potassium chlorate, said iodate is potassium iodate, and said periodate is ammonium periodate.
5. A chemical mechanical polishing slurry of Claim 1, wherein the weight concentration of said oxidants is in the range of 0.5-4%.
6. A chemical mechanical polishing slurry of Claim 1, wherein said amino acids are selected from glycine and/ or L- glutamic acid.
7. A chemical mechanical polishing slurry of Claim 1, wherein the weight concentration of said amino acids is in the range of 1-8%.
8. A chemical mechanical polishing slurry of Claim 1, wherein said quaternary ammonium bases are tetramethylammonium hydroxide.
9. A chemical mechanical polishing slurry of Claim 1, wherein the pH of said chemical mechanical polishing slurry ranges from 8.00-13.00.